

Kevin Lee

List of Publications by Year in descending order

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17
papers

592
citations

758635

12
h-index

996533

15
g-index

17
all docs

17
docs citations

17
times ranked

796
citing authors

#	ARTICLE	IF	CITATIONS
1	MBE-grown 232â€“270â€“nm deep-UV LEDs using monolayer thin binary GaN/AlN quantum heterostructures. Applied Physics Letters, 2017, 110, .	1.5	105
2	High Breakdown Voltage in RF AlN/GaN/AlN Quantum Well HEMTs. IEEE Electron Device Letters, 2019, 40, 1293-1296.	2.2	79
3	Crystal orientation dictated epitaxy of ultrawide-bandgap 5.4- to 8.6-eV $\hat{\Gamma}$ ±-(AlGa) ₂ O ₃ on m-plane sapphire. Science Advances, 2021, 7, .	4.7	71
4	GaN HEMTs on Si With Regrown Contacts and Cutoff/Maximum Oscillation Frequencies of 250/204 GHz. IEEE Electron Device Letters, 2020, 41, 689-692.	2.2	69
5	Deep-UV emission at 219â€“nm from ultrathin MBE GaN/AlN quantum heterostructures. Applied Physics Letters, 2017, 111, .	1.5	54
6	Development of GaN Vertical Trench-MOSFET With MBE Regrown Channel. IEEE Transactions on Electron Devices, 2018, 65, 2558-2564.	1.6	46
7	Activation of buried p-GaN in MOCVD-regrown vertical structures. Applied Physics Letters, 2018, 113, 062105.	1.5	35
8	Molecular beam homoepitaxy on bulk AlN enabled by aluminum-assisted surface cleaning. Applied Physics Letters, 2020, 116, .	1.5	26
9	Surface control and MBE growth diagram for homoepitaxy on single-crystal AlN substrates. Applied Physics Letters, 2020, 116, .	1.5	26
10	Enhanced injection efficiency and light output in bottom tunnel-junction light-emitting diodes. Optics Express, 2020, 28, 4489.	1.7	19
11	MBE growth and donor doping of coherent ultrawide bandgap AlGaIn alloy layers on single-crystal AlN substrates. Applied Physics Letters, 2021, 118, .	1.5	16
12	Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. Applied Physics Letters, 2021, 119, .	1.5	15
13	Light-emitting diodes with AlN polarization-induced buried tunnel junctions: A second look. Applied Physics Letters, 2020, 117, .	1.5	11
14	Enhanced efficiency in bottom tunnel junction InGaIn blue LEDs. , 2021, , .		6
15	Dislocation and indium droplet related emission inhomogeneities in InGaIn LEDs. Journal Physics D: Applied Physics, 2021, 54, 495106.	1.3	6
16	Bottom tunnel junction blue light-emitting field-effect transistors. Applied Physics Letters, 2020, 117, 031107.	1.5	5
17	Efficient InGaIn p-Contacts for deep-UV Light Emitting Diodes. , 2019, , .		3